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Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 5861135 A

L6: Entry 1 of 4

File: USPT

Jan 19, 1999

US-PAT-NO: 5861135

DOCUMENT-IDENTIFIER: US 5861135 A

TITLE: Highly crystalline diamond

DATE-ISSUED: January 19, 1999

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Tanabe; Keiichiro Fujimori; Naoji Hyogo-ken Hyogo-ken N/A N/A

JPX JPX

US-CL-CURRENT: 423/446

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

2. Document ID: US 5776552 A

L6: Entry 2 of 4

File: USPT

Jul 7, 1998

US-PAT-NO: 5776552

DOCUMENT-IDENTIFIER: US 5776552 A

TITLE: Process for the vapor phase synthesis of diamond and highly crystalline

diamond

DATE-ISSUED: July 7, 1998

INVENTOR-INFORMATION:

NAME Tanabe; Keiichiro CITY Hyogo-ken STATE

ZIP CODE

COUNTRY

JPX

JPX

Tanabe; Keiichir Fujimori; Naoji

Hyogo-ken

N/A

N/A

N/A N/A

US-CL-CURRENT: 427/577; 117/104, 423/446

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Desc Image

3. Document ID: US 5646924 A

L6: Entry 3 of 4

File: USPT

Jul 8, 1997

المارية



US-PAT-NO: 5646924

DOCUMENT-IDENTIFIER: US 5646924 A

TITLE: Recording and simultaneous verifying method of phase-changing type of

information recording medium

DATE-ISSUED: July 8, 1997

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Nonoyama; Osamu	Yokohama	N/A	N/A	JPX
Ide; Yukio	Mishima	N/A	N/A	JPX
Harigaya; Makoto	Hiratsuka	N/A	N/A	JPX
Kageyama; Yoshiyuki	Yokohama	N/A	N/A	JPX
Deguchi; Hiroshi	Yokohama	N/A	N/A	JPX
Yamada; Katsuyuki	Mishima	N/A	N/A	JPX
Takahashi; Masaetsu	Yokohama	N/A	N/A	JPX
Iwasaki; Hiroko	Tokyo	N/A	N/A	JPX

US-CL-CURRENT: 369/53.36; 369/116, 369/275.1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	K000C	Drawl Desc	Image

4. Document ID: US 5270263 A

L6: Entry 4 of 4

File: USPT

Dec 14, 1993

US-PAT-NO: 5270263

DOCUMENT-IDENTIFIER: US 5270263 A

TITLE: Process for depositing aluminum nitride (AlN) using nitrogen plasma

sputtering

DATE-ISSUED: December 14, 1993

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kim; Sung C.	Boise	ID	N/A	N/A
Yu; Chris C.	Boise	ID	N/A	N/A
Doan; Trung T.	Boise	ID	N/A	N/A

US-CL-CURRENT: 438/702; 204/192.22, 204/192.25, 438/717, 438/740, 438/761

			<u> </u>						
Full Title 0	Citation Front	Review	Classification	Date	Reference	Claims	KWIC	Draw, Desc	Image

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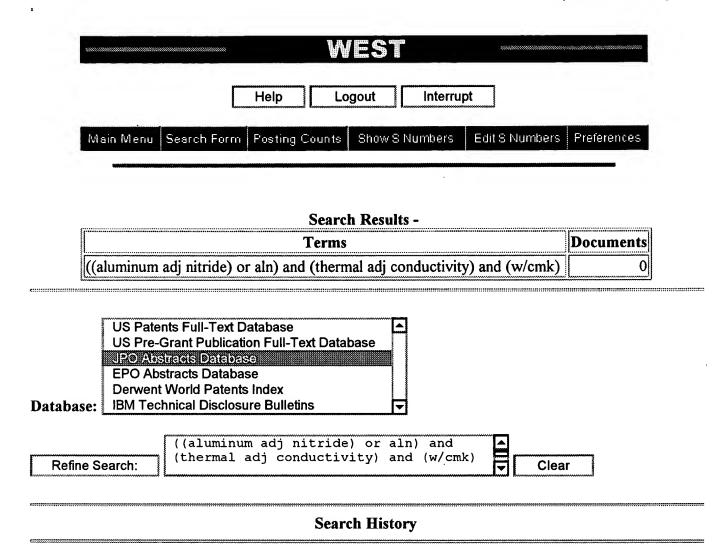
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(w/cmk)	4

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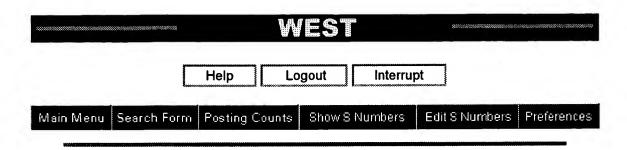
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JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L7</u>
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JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L5</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cmk)	0	<u>L4</u>
РСРВ, ЈРАВ	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cm adj k)	0	<u>L3</u>
РСРВ, ЈРАВ	((aluminum adj nitride) or aln) and (thermal adj conductivity)	656	<u>L2</u>
PGPB	semiconductor	0	<u>L1</u>



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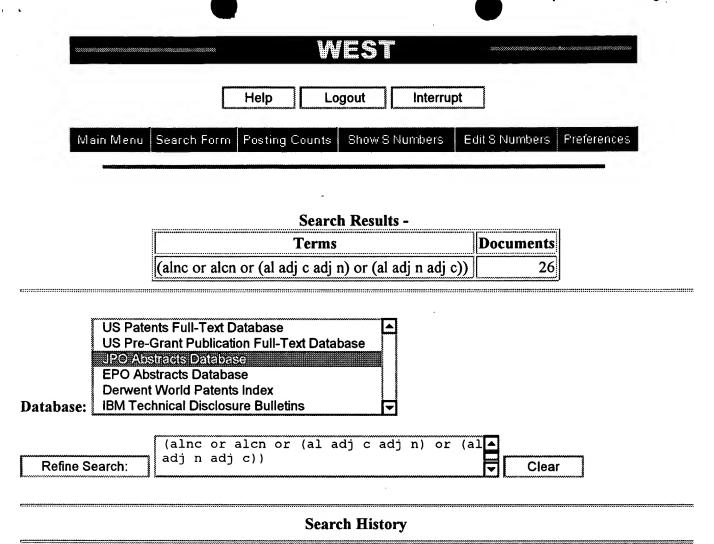
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((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and Clear

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DB Name	<u>Ouery</u>	Hit Count	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<u>L5</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<u>L4</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<u>L3</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<u>L2</u>
ЈРАВ	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<u>L1</u>



Today's Date: 3/13/2001

